

Features

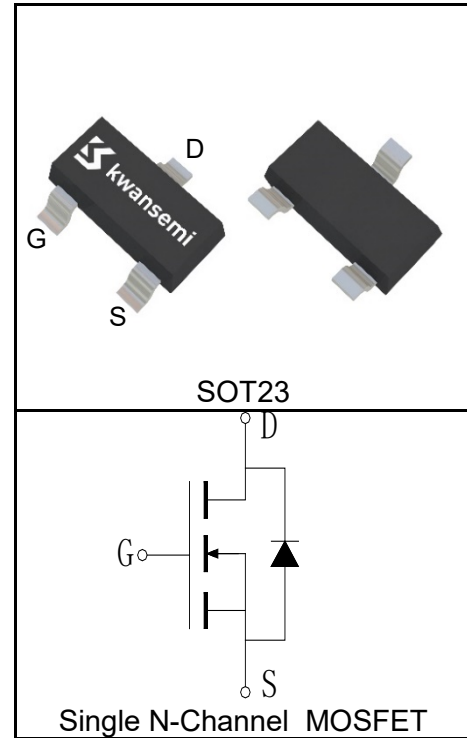
- 60V/3A,
 $R_{DS(ON)} = 60m\Omega(Typ.)@V_{GS}=10V$
 $R_{DS(ON)} = 70m\Omega(Typ.)@V_{GS}=4.5V$
- Super High Dense Cell Design
- Fast Switching Speed

Applications

- Load Switch
- Power Management



Pin Description



Absolute Maximum Ratings

Symbol	Parameter		Rating	Unit
Common Ratings (T _A =25°C Unless Otherwise Noted)				
V _{DSS}	Drain-Source Voltage		60	V
V _{GSS}	Gate-Source Voltage		±20	
T _{Jmax}	Maximum Junction Temperature		150	°C
T _J ,T _{STG}	Operating and Storage Temperature Range		-55 to 150	°C
I _S	Diode Continuous Forward Current	T _A =25°C	1.4	A
Mounted on Large Heat Sink				
I _{DP} ^①	300μs Pulse Drain Current Tested	T _A =25°C	12	A
I _D ^②	Continuous Drain Current(V _{GS} =10V)	T _A =25°C	3	A
		T _A =70°C	2.4	
P _D	Maximum Power Dissipation	T _A =25°C	1	W
		T _A =70°C	0.64	
R _{θJL}	Thermal Resistance-Junction to Lead		80	°C/W
R _{θJA} ^③	Thermal Resistance-Junction to Ambient		125	°C/W
Drain-Source Avalanche Ratings				
E _{AS} ^④	Avalanche Energy, Single Pulsed		16	mJ

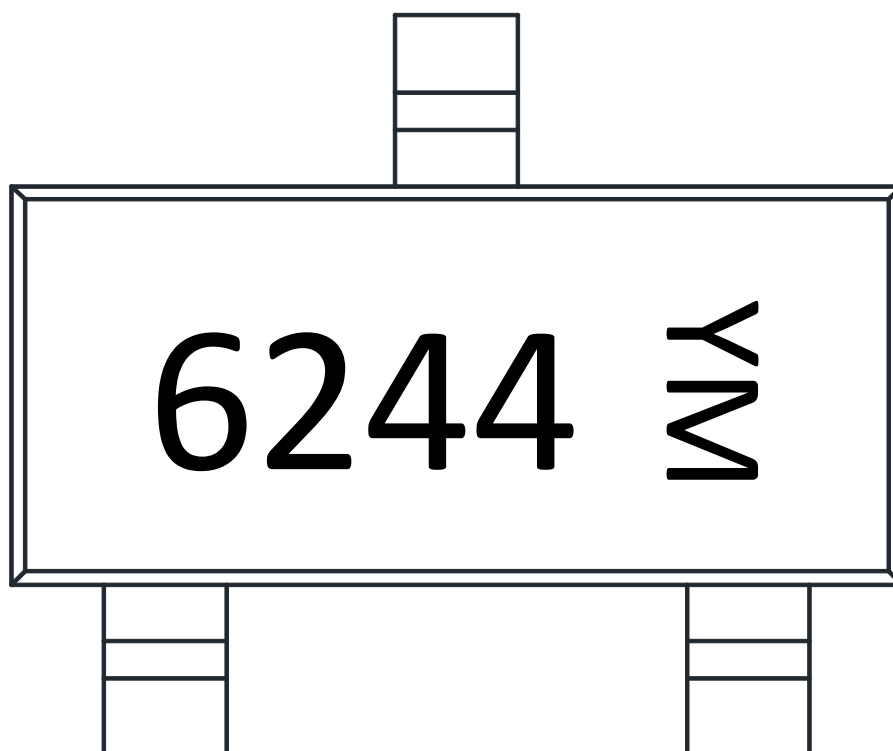
Electrical Characteristics ($T_A=25^{\circ}\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Condition	KS6244AA			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	60			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =60V, V _{GS} =0V			1	μA
			T _J =125°C		30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	1.2	1.5	2.3	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V			±100	nA
R _{DS(ON)} ^⑤	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =3A		60	72	mΩ
		V _{GS} =4.5V, I _{DS} =2A		70	90	mΩ
Diode Characteristics						
V _{SD} ^⑤	Diode Forward Voltage	I _{SD} =3A, V _{GS} =0V		0.83	1.2	V
t _{rr}	Reverse Recovery Time	I _{SD} =3A, dI _{SD} /dt=100A/μs		22		ns
Q _{rr}	Reverse Recovery Charge			10		nC
Dynamic Characteristics ^⑥						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz		2.1		Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =30V, Frequency=1.0MHz		535		pF
C _{oss}	Output Capacitance			40		
C _{rss}	Reverse Transfer Capacitance			25		
t _{d(ON)}	Turn-on Delay Time	V _{DD} =30V, I _{DS} =3A, V _{GEN} =10V, R _G =6Ω		8		ns
t _r	Turn-on Rise Time			13		
t _{d(OFF)}	Turn-off Delay Time			25		
t _f	Turn-off Fall Time			12		
Gate Charge Characteristics ^⑥						
Q _g	Total Gate Charge	V _{DS} =30V, V _{GS} =10V, I _{DS} =3A		12		nC
Q _{gs}	Gate-Source Charge			1.2		
Q _{gd}	Gate-Drain Charge			2.4		

- Notes:
- ① Pulse width limited by safe operating area.
 - ② Calculated continuous current based on maximum allowable junction temperature.
 - ③ When mounted on 1 inch square copper board, $t \leq 10\text{sec}$. The value in any given application depends on the user's specific board design.
 - ④ Limited by T_{Jmax} , Starting $T_J = 25^{\circ}\text{C}$, $I_{ASmax} = 8A$, $L = 0.5\text{mH}$, $V_{DD}=48V$, $R_G = 25\Omega$, $V_{GS} = 10V$. Part not recommended for use above this value.
 - ⑤ Pulse test; Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
 - ⑥ Guaranteed by design, not subject to production testing.

Ordering and Marking Information

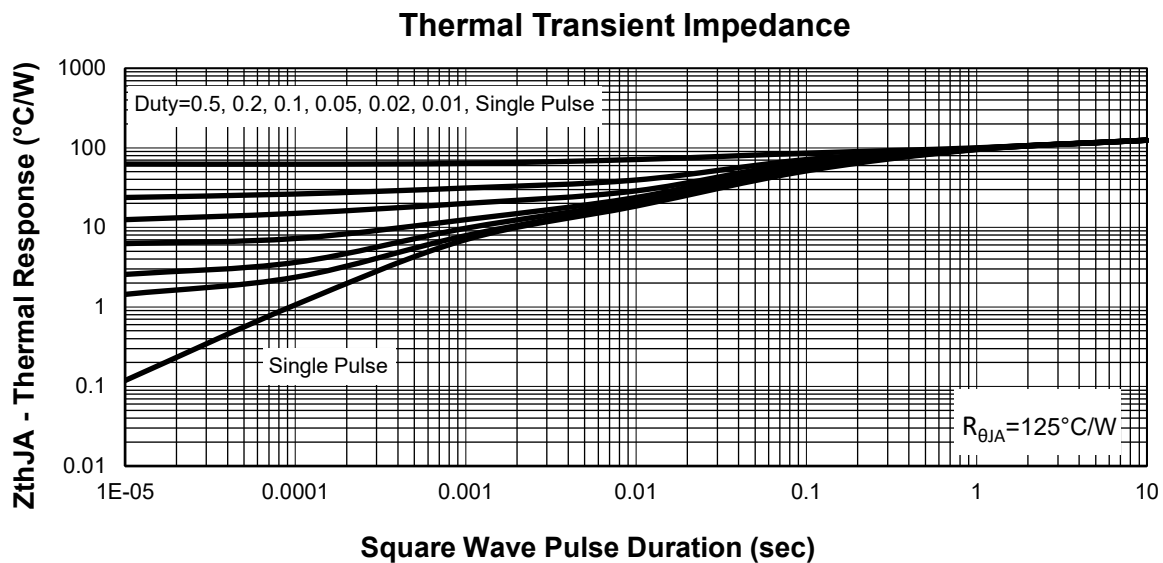
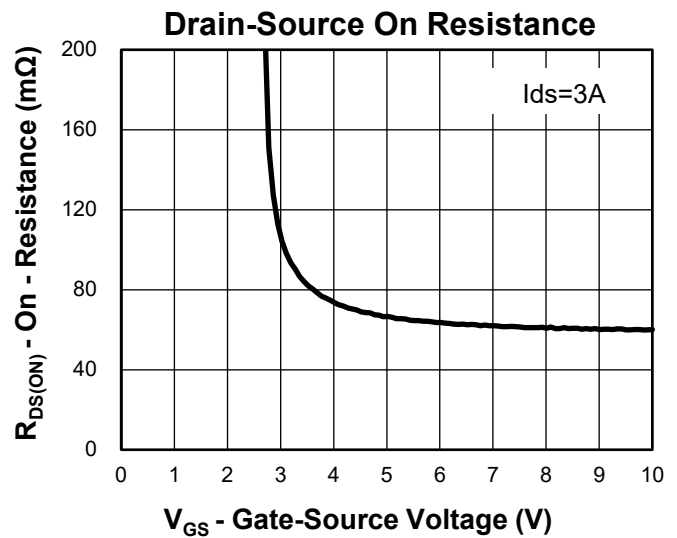
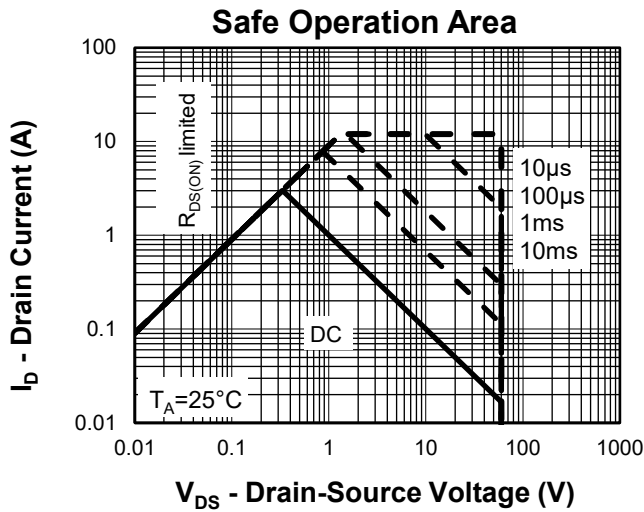
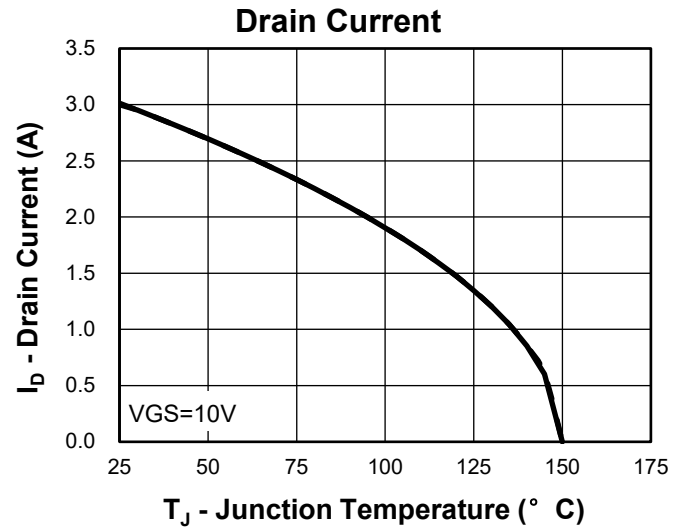
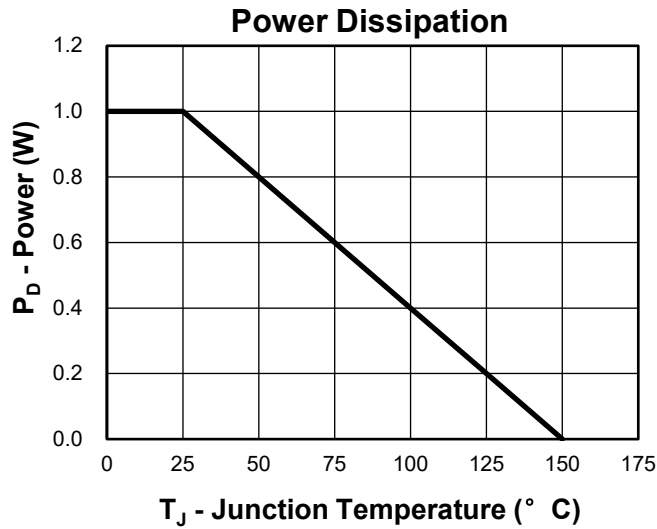
Device	Package	Packaging	Quantity	Reel Size	Tape width
KS6244AA	SOT23	Tape&Reel	3000	7"	8mm



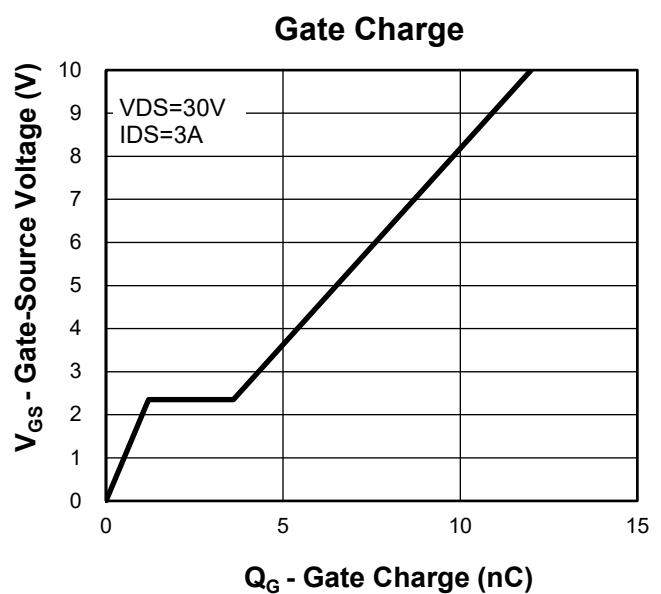
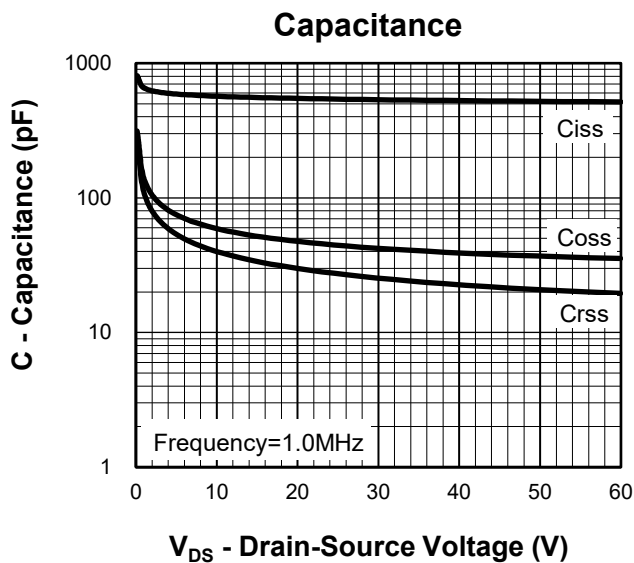
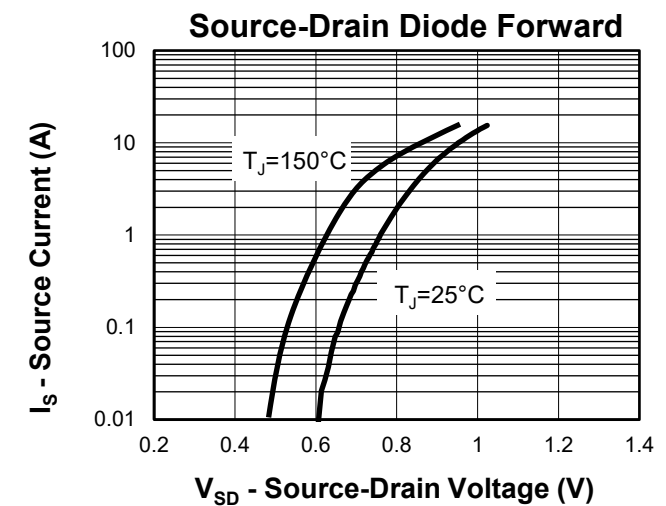
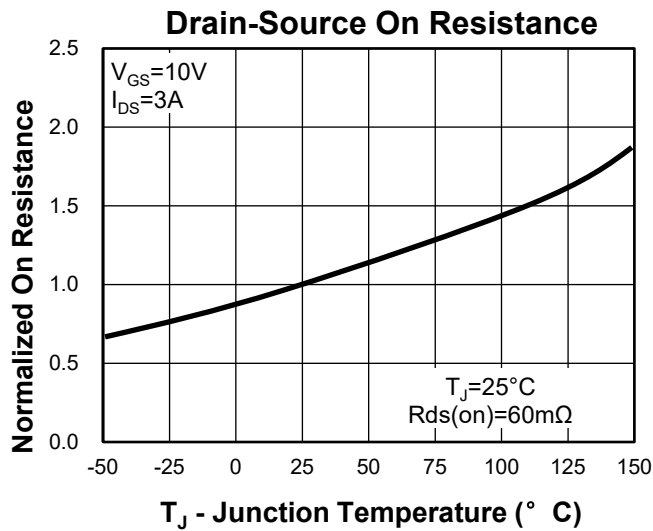
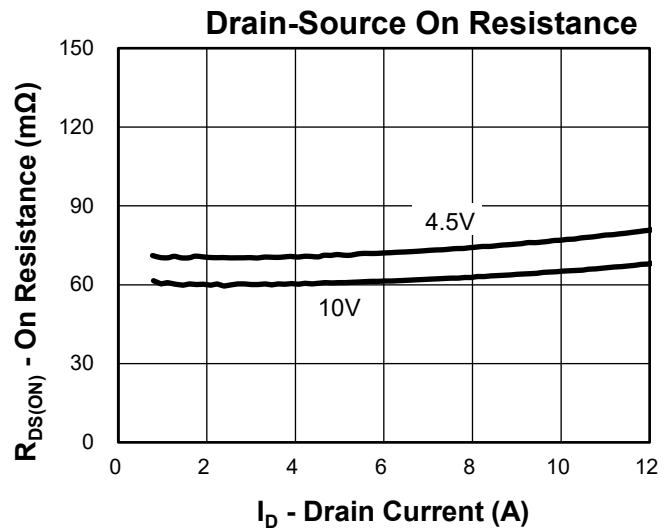
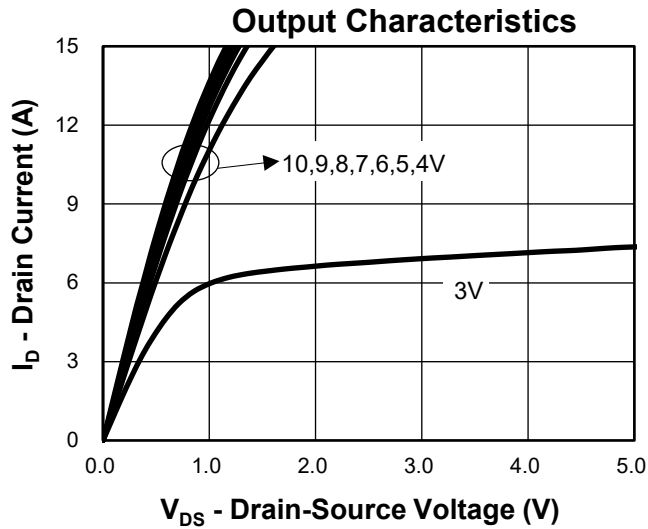
Y =Year,2017-A,2018-B,etc.

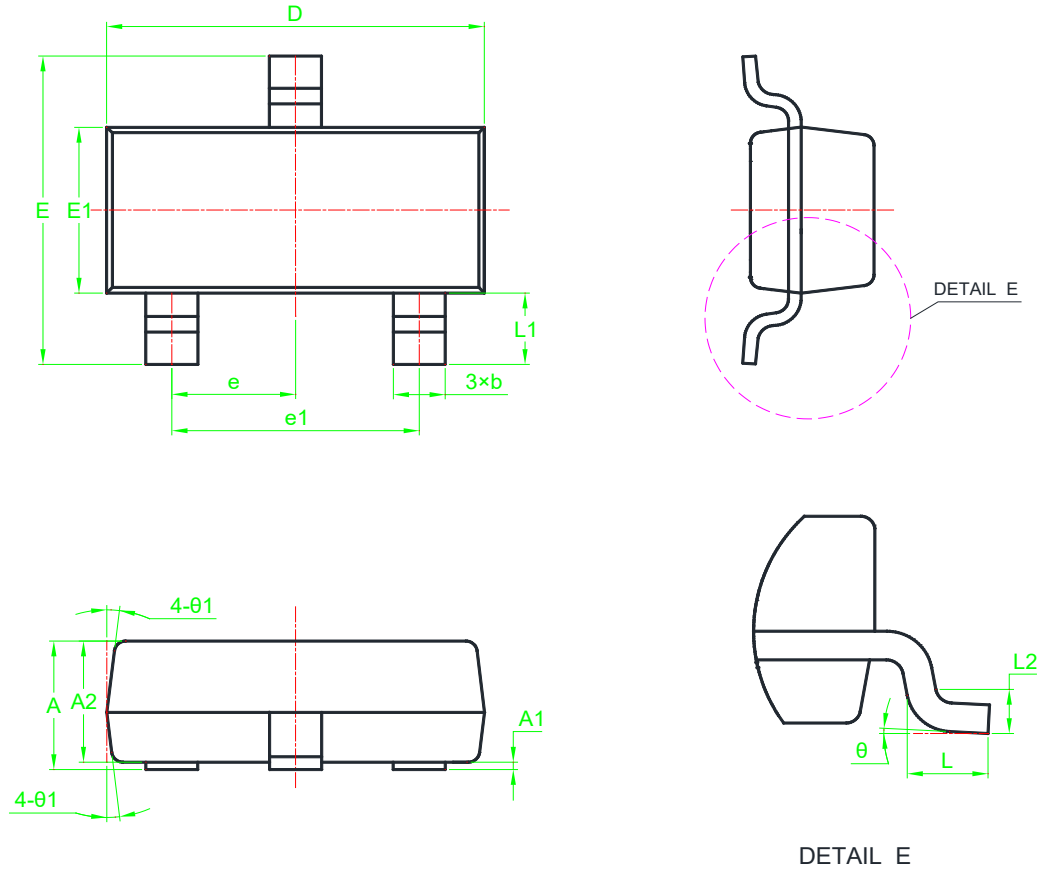
M =Month,Jan-1,Feb-2,....Sep-9,Oct-A,Nov-B,Dec-C.

Typical Characteristics



Typical Characteristics

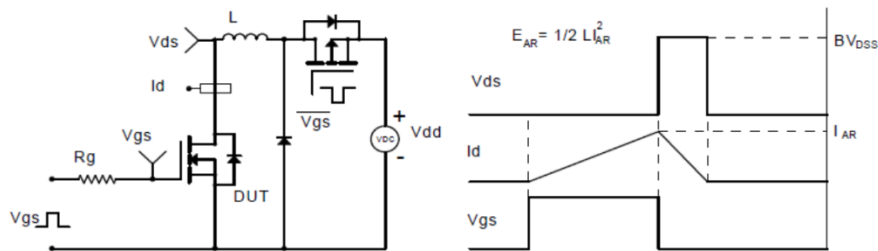


Package Information
SOT23


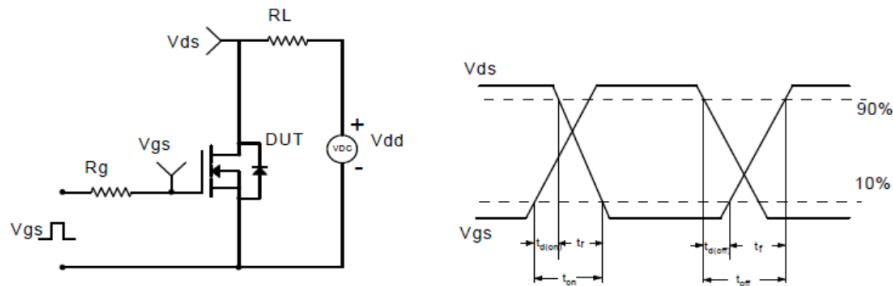
SYMBOL	MM			INCH			SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX		MIN	NOM	MAX	MIN	NOM	MAX
A	0.90	*	1.12	0.035	*	0.044	e	0.95BSC			0.037BSC		
A1	0.01	*	0.10	0.000	*	0.004	e1	1.90BSC			0.075BSC		
A2	0.80	0.90	1.02	0.031	0.035	0.040	L	0.30	0.40	0.50	0.012	0.016	0.020
b	0.30	0.40	0.50	0.012	0.016	0.020	L1	0.54REF			0.021REF		
D	2.80	2.90	3.00	0.110	0.114	0.118	L2	0.254BSC			0.010BSC		
E	2.25	2.40	2.55	0.089	0.094	0.100	θ	0°	*	8°	0°	*	8°
E1	1.20	1.30	1.40	0.047	0.051	0.055	θ1	0°	*	10°	0°	*	10°

Note: Dimensions do not inclusive burrs and mold flash.

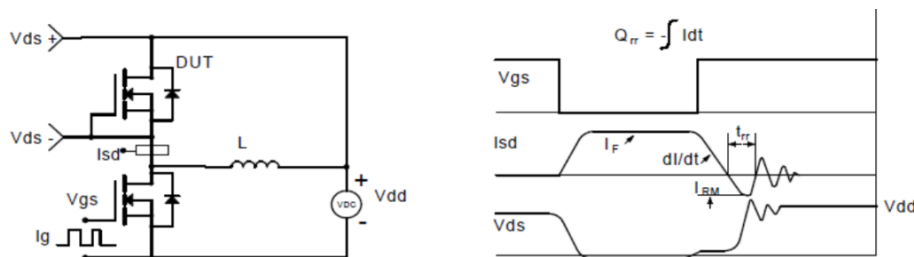
Avalanche Test Circuit and Waveforms



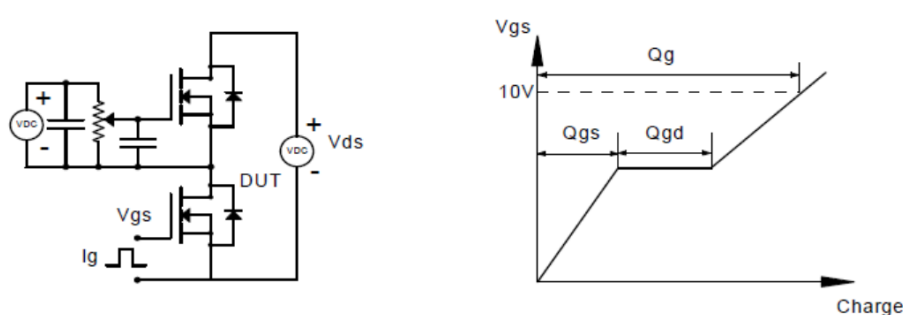
Switching Time Test Circuit and Waveforms



Diode Recovery Test Circuit and Waveforms



Gate Charge Test Circuit and Waveform



Customer Service

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